

N-channel TrenchMOS logic level FET Rev. 02 — 31 January 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

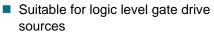
1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- 1.3 Applications
 - 12 V and 24 V loads
 - Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	46	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	105	W



- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids



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Table 1.	Quick reference da	tacontinued					
Symbol	Parameter	Conditions	Γ	Min	Тур	Max	Unit
Static cha	racteristics						
R _{DSon} drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	-	-	26	mΩ	
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	•	19	21.7	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } Figure 12;$ see Figure 13	-	•	20	24	mΩ
Avalanche	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 46 \text{ A}; \text{V}_{\text{sup}} \leq 25 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 5 \text{ V}; \\ T_{\text{j(init)}} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	•	-	76	mJ

	Table '	1. (Quick	reference	data	continued
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Pinning information 2.

Nexperia

Table 2.	Pinning	Pinning information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate		-	
2	D	drain	mb		
3	S	source			
mb	D	mounting base; connected to drain		mbb076 S	

SOT404 (D2PAK)

Ordering information 3.

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
BUK9624-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

Limiting values 4.

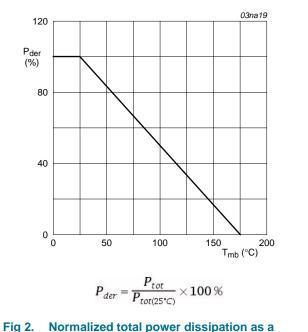
Limiting values Table 4.

In accordance with the Absolute Maximum Rating System (IEC 60134).

		5, (
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-10	10	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	46	A
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	33	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s};$ see <u>Figure 3</u>	-	188	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	105	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 µs	-15	15	V
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	46	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	188	А
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 46 \text{ A}; V_{sup} \le 25 \text{ V}; R_{GS} = 50 \Omega;$ V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped	-	76	mJ

03aa24 120 l_{der} (%) 80 40 0 150 200 T_{mb} (°C) 0 50 100 $I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$ Fig 1. Normalized continuous drain current as a

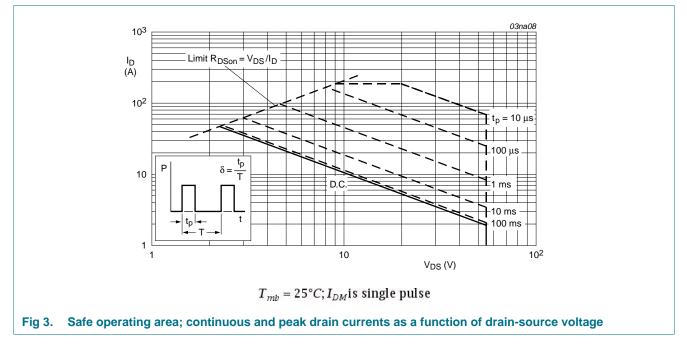
function of mounting base temperature





BUK9624-55A

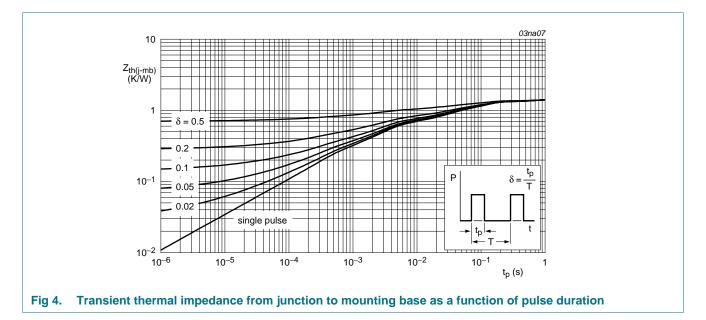
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air; lead length ≤ 5 mm; see <u>Figure 4</u>	-	50	-	K/W

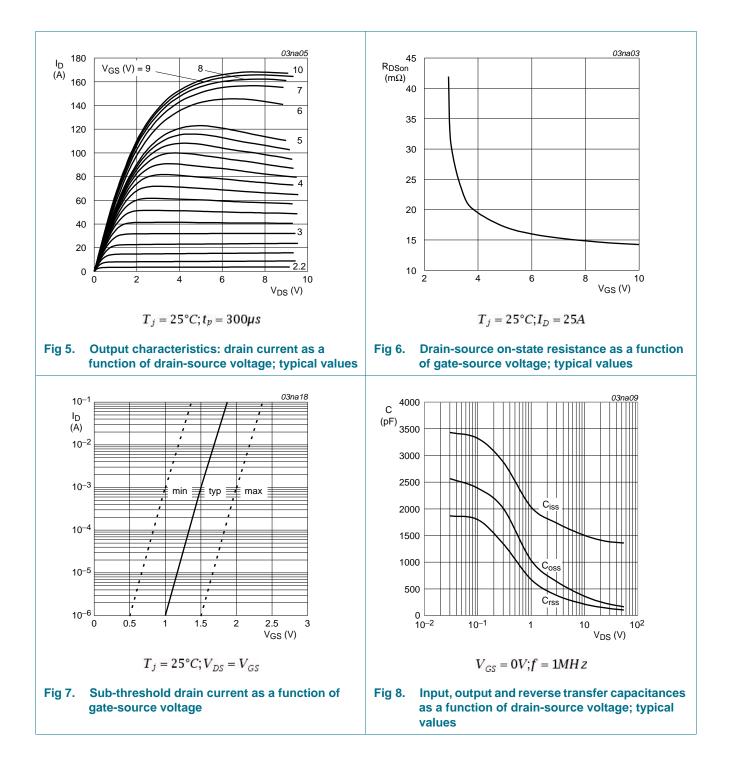


6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	26	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	19	21.7	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	20	24	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1361	1815	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 8$	-	239	287	pF
C _{rss}	reverse transfer capacitance		-	162	222	pF
t _{d(on)}	turn-on delay time	$V_{DS}=30 \text{ V}; \text{ R}_{L}=1.2 \Omega; V_{GS}=5 \text{ V}; \label{eq:VDS}$	-	17.5	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	104	-	ns
t _{d(off)}	turn-off delay time		-	82.5	-	ns
t _f	fall time		-	80	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 14</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 46 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	50	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _i = 25 °C	-	85	-	nC

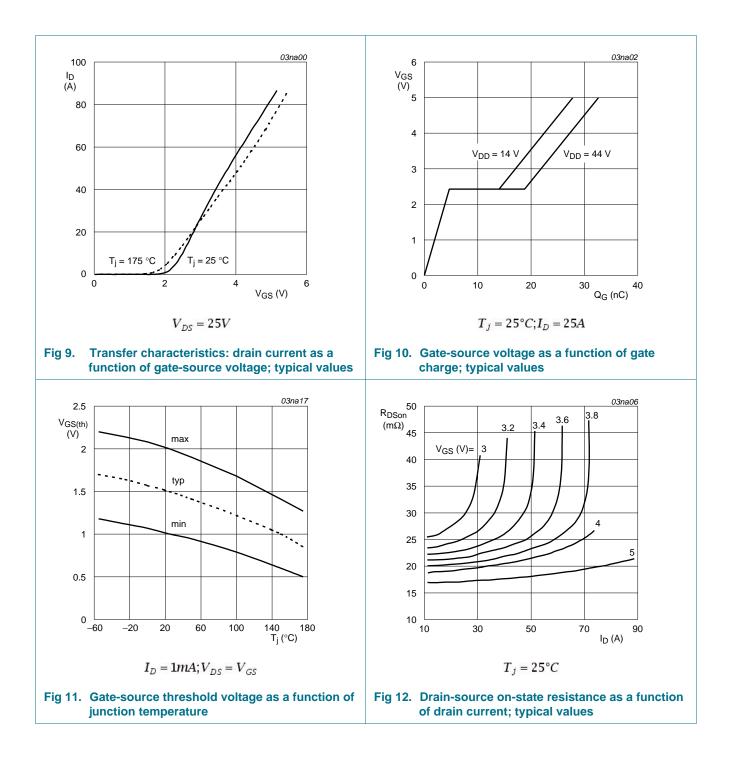
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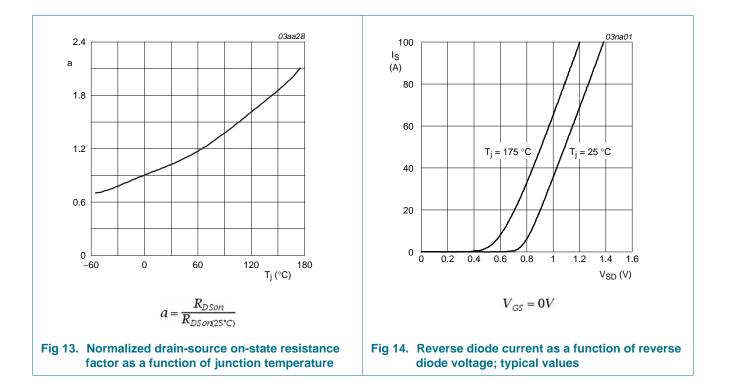
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7. Package outline

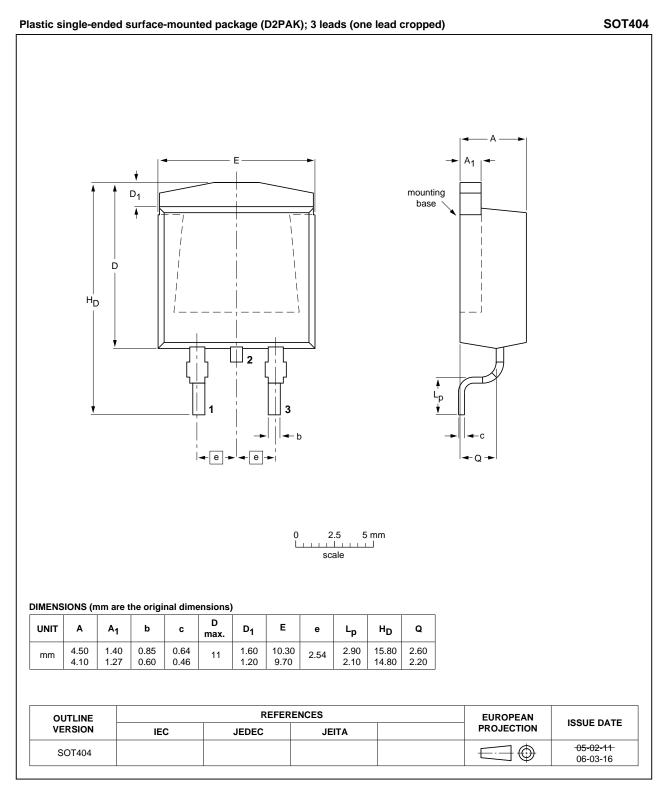


Fig 15. Package outline SOT404 (D2PAK)

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BUK9624-55A

8. Revision history

Table 7. Revision hist	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9624-55A v.2	20110131	Product data sheet	-	BUK9524_9624_55A v.1
Modifications:	 The format of this of NXP Semicono 		esigned to comply with	n the new identity guidelines
	 Legal texts have 	been adapted to the new	company name where	e appropriate.
	 Type number BU 	K9624-55A separated fro	m data sheet BUK952	24_9624_55A v.1.
	 Various changes 	to content.		
BUK9524_9624_55A v.1	20000929	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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